



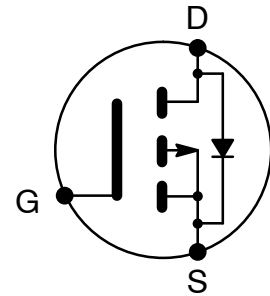
ELECTRONICS, INC.  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089  
<http://www.nteinc.com>



**NTE2918**  
**MOSFET**  
**P-Ch, Enhancement Mode**  
**High Speed Switch**  
**TO220 Type Package**

**Features:**

- Dynamic dv/dt Rating
- +175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated



**Absolute Maximum Ratings:**

Continuous Drain Current ( $V_{GS} = -10V$ ), $I_D$	
$T_C = +25^\circ C$ .....	-31A
$T_C = +100^\circ C$ .....	-22A
Pulsed Drain Current (Note 1), $I_{DM}$ .....	-110A
Power Dissipation ( $T_C = +25^\circ C$ ), $P_D$ .....	110W
Derate Linearly Above $25^\circ C$ .....	0.71W/ $^\circ C$
Gate-to-Source Voltage, $V_{GS}$ .....	$\pm 20$
Single Pulse Avalanche Energy (Note 2), $E_{AS}$ .....	280mJ
Avalanche Current (Note 1), $I_{AR}$ .....	-16A
Repetitive Avalanche Energy (Note 1), $E_{AR}$ .....	11mJ
Peak Diode Recovery dv/dt (Note 3), dv/dt .....	-5.0V/ns
Operating Junction Temperature Range, $T_J$ .....	-55° to +175°C
Storage Temperature Range, $T_{stg}$ .....	-55° to +175°C
Lead Temperature (During Soldering, 1.6mm from case for 10sec), $T_L$ .....	+300°C
Mounting Torque (6-32 or M3 Screw) .....	10 lbf•in (1.1N•m)
Thermal Resistance, Junction-to-Case, $R_{thJC}$ .....	1.4°C/W
Thermal Resistance, Junction-to-Ambient, $R_{thJA}$ .....	62°C/W
Typical Thermal Resistance, Case-to-Sink (Flat, Greased Surface), $R_{thCS}$ .....	0.5°C/W

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 2.  $V_{DD} = -25V$ , starting  $T_J = +25^\circ C$ ,  $L = 2.1mH$ ,  $R_G = 25\pm$ ,  $I_{AS} = -16A$

Note 3.  $I_{SD} \leq -16A$ ,  $di/dt \leq -280A/\mu s$ ,  $V_{DD} \leq -55V$ ,  $T_J \leq +175^\circ C$

Note 4. Pules Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .

**Electrical Characteristics:** ( $T_J = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-55	-	-	V
Breakdown Voltage Temp. Coefficient	$\frac{V_{(BR)DSS}}{T_J}$	Reference to $+25^\circ\text{C}$ , $I_D = -1mA$	-	-0.034	-	V/ $^\circ\text{C}$
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -16A$ , Note 4	-	-	0.06	$\pm$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-2.0	-	-4.0	V
Forward Transconductance	$g_{fs}$	$V_{DS} = -25V, I_D = -16A$	8.0	-	-	mhos
Drain-to-Source Leakage Current	$I_{DSS}$	$V_{DS} = -55V, V_{GS} = 0V$	-	-	-25	$\leq A$
		$V_{DS} = -44V, V_{GS} = 0V, T_J = +125^\circ\text{C}$	-	-	-250	$\leq A$
Gate-to-Source Forward Leakage	$I_{GSS}$	$V_{GS} = 20V$	-	-	100	nA
Gate-to-Source Reverse Leakage	$I_{GSS}$	$V_{GS} = -20V$	-	-	-100	nA
Total Gate Charge	$Q_g$	$I_D = -16A, V_{DS} = -44V, V_{GS} = -10V$ , Note 4	-	-	63	nC
Gate-to-Source Charge	$Q_{gs}$		-	-	13	nC
Gate-to-Drain ("Miller") Charge	$Q_{gd}$		-	-	29	nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -28V, I_D = -16A, R_G = 6.8\pm$ , $R_D = 1.6\pm$ , Note 4	-	14	-	ns
Rise Time	$t_r$		-	66	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	39	-	ns
Fall Time	$t_f$		-	63	-	ns
Internal Drain Inductance	$L_D$	Between lead, .250in. (6.0) mm from package and center of die contact	-	4.5	-	nH
Internal Source Inductance	$L_S$		-	7.5	-	nH
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = -25V, f = 1MHz$	-	1200	-	pF
Output Capacitance	$C_{oss}$		-	520	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	250	-	pF

**Source-Drain Ratings and Characteristics:**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Source Current (Body Diode)	$I_S$		-	-	-31	A
Pulsed Source Current (Body Diode)	$I_{SM}$	Note 1	-	-	-110	A
Diode Forward Voltage	$V_{SD}$	$T_J = +25^\circ\text{C}, I_S = -16A, V_{GS} = 0V$ , Note 4	-	-	-1.3	V
Reverse Recovery Time	$t_{rr}$	$T_J = +25^\circ\text{C}, I_F = -16A$ , $di/dt = -100A/\mu s$ , Note 4	-	71	110	ns
Reverse Recovery Charge	$Q_{rr}$		-	170	250	nC

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 4. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

